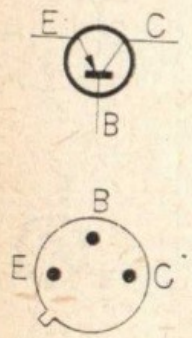


Type	Operational Data		Maximum Ratings
<p>KF517</p>  <p>Silicon p-n-p planar epitaxial transistors for R. F. amplifiers Complementary to KF 507</p>	<p>$-I_{CBO}$ < 500 nA $-I_{CEO}$ < 1 μA $-U_{CBO}$ > 40 V $-U_{EBO}$ > 5 V $-U_{CES}$ < 1,5 V $-I_{B2}$ < 500 μA h_{21E} > 20 $-I_{B3}$ < 7 mA h_{21E} > 20 h_{21E} > 10 f_T > 40 MHz C_{22b} < 30 pF h_{11} 2,2 kΩ h_{12} 2,2 $\cdot 10^{-4}$ h_{21} 50 h_{22} 12,5 μS</p>	<p>measured at $-U_{CB} = 30$ V $-U_{CE} = 10$ V, $R_{BE} = \infty$ $-I_{CBO} = 100$ μA $-U_{EBO} = 100$ μA $-I_C = 150$ mA, $-I_B = 15$ mA $-U_{CB} = 10$ V, $I_E = 10$ mA $-U_{CB} = 10$ V, $I_E = 150$ mA $-U_{CB} = 10$ V, $I_E = 500$ mA $-U_{CB} = 10$ V, $I_E = 50$ mA, $f = 30$ MHz $-U_{CB} = 10$ V, $I_E = 0$ mA, $f = 2$ MHz $-U_{CE} = 5$ V, $-I_C = 1$ mA, $f = 1$ kHz</p>	<p>$-U_{CBO}$ 40 V $-U_{CEO}^{3)}$ 32 V $-U_{EBO}$ 5 V $-I_C$ 500 mA I_E 500 mA $-I_B$ 50 mA $PC^{1)}$ 0,8 W $PC^{2)}$ 2,6 W T_j +200 $^{\circ}$C T_a -65...+200 $^{\circ}$C $R_{\theta 1}$ 60 $^{\circ}$C/W R_{θ} 220 $^{\circ}$C/W</p> <p>1) Without cooling 2) With ideal cooling 3) $R_{BE} \leq 10 \Omega$</p>
Outlines K 505			